

DATE: April 27, 2026

PCN #: 2811

PCN Title: Additional wafer source (SPFAB), additional Internal AT site (CAT) with standardized (BOM)

Dear Customer:

This is an announcement of change(s) to products that are currently being offered by Diodes Incorporated.

We request that you acknowledge receipt of this notification within 30 days of the date of notification by contacting your local Diodes sales representative. If you require samples for evaluation purposes, please submit a corresponding request within 30 days as well. Otherwise, samples may not be built prior to the implementation of the announced change(s).

The change(s) announced in this PCN will not be implemented prior to the target implementation date, i.e. 90 days from the stated notification date, unless Diodes receives written customer approval before that date.

Previously agreed upon customer specific product and/or process change requirements will be addressed separately.

For questions or clarification regarding this PCN, please contact your local Diodes sales representative.

Sincerely,

Diodes Incorporated PCN Team



PRODUCT CHANGE NOTICE

PCN-2811-REV1

Notification Date:	Implementation Date:	Product Family:	Change Type:	PCN #:
April 27, 2026	July 26, 2026	Analog	Additional wafer source (SPFAB), additional AT source	2811
TITLE				
Additional Wafer Source (SPFAB), additional Internal AT site (CAT) with standardized (BOM)				
DESCRIPTION OF CHANGE				
This PCN is being issued to notify customers that in order to assure continuity of supply, Diodes has qualified additional internal wafer source (SPFAB) located in South Portland, Maine, USA and Diodes internal A/T Site (CAT) located in Chengdu, China. Full electrical characterization and reliability testing have been completed on representative part numbers to ensure there is no change to product reliability, device functionality or electrical specifications in the datasheet unless specified.				
IMPACT				
Continuity of Supply - There will be no change to the Form, Fit, or Function of affected products unless specified.				
PRODUCTS AFFECTED				
Table 1 - Additional wafer source (SPFAB), additional Internal AT site (CAT) with standardized (BOM)				
Table 2 - Additional wafer source (SPFAB)				
WEB LINKS				
Manufacturer's Notice:	https://www.diodes.com/quality/product-change-notices/diodes-product-change-notices/			
For More Information Contact:	https://www.diodes.com/about/contact-us/contact-sales/			
Data Sheet:	https://www.diodes.com/catalog/			
DISCLAIMER				
Unless a Diodes Incorporated Sales representative is contacted in writing within 30 days from the notification date of this PCN, all changes described in this announcement are considered approved.				

Table 1 - Additional wafer source (SPFAB), additional Internal AT site (CAT) with standardized (BOM)

74LVC1G3157FZ4-7					
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Table 2 - Additional wafer source (SPFAB)

74LVC1G3157DW-7	AP7361C-10FGE-7	AP7361C-12FGE-7	AP7361C-15FGE-7	AP7361C-18FGE-7	AP7361C-25FGE-7
AP7361C-28FGE-7	AP7361C-33FGE-7	AP7361C-FGE-7	AP7361E-10FGE-7	AP7361E-12FGE-7	AP7361E-15FGE-7
AP7361E-18FGE-7	AP7361E-25FGE-7	AP7361E-28FGE-7	AP7361E-33FGE-7	AP7361EA-10FGE-7	AP7361EA-10FGE-7A
AP7361EA-18FGE-7	AP7361EA-18FGE-7A	AP7361EA-33FGE-7	AP7361EA-33FGE-7A	AP7361EA-FGE-7	AP7361EA-FGE-7A
AP7361E-FGE-7					

Certificate of Design, Construction & Qualification



Description: AP7361Px-xxFGE-7 Standard Qual Plan (A follow-on product of group 1 family)

				Qual Device 1		Qual Device 2		Qual Device 3		QBS Device 1		QBS Device 2		QBS Device 3		QBS Device 4		QBS Device 5		QBS Device 6		QBS Device 7		QBS Device 8		QBS Device 9		QBS Device 10		QBS Device 11							
General	Part Number			AP7361PE-FGE-7 (AP7361C-XXFGE-7 AP7361E-XXFGE-7 AP7361EA-XXFGE-7)		AP7361P-FGE-7 (AP7361C-XXFGE-7 AP7361E-XXFGE-7 AP7361EA-XXFGE-7)		AP7361P-FGE-7 (AP7361C-XXFGE-7 AP7361E-XXFGE-7 AP7361EA-XXFGE-7)		AP7361EA-FGE-7		AP7361EA-FGE-7		AP7361EA-FGE-7		AP7361E-FGE-7		AP7361EA-33SP-13		AP7361EA-33SP-13		AP7361EA-33SP-13		AP7340Q-33FS4-7/ AP7340-33FS4-7		AP7340Q-33FS4-7/ AP7340-33FS4-7		AP7340Q-33FS4-7/ AP7340-33FS4-7		AP7340Q-33FS4-7/ AP7340-33FS4-7							
	Die Revision			AD08070637C0-SP		AD08070637C0-SP		AD08070637C0-SP		TN017E0-2		TN017E0-2		TN017E0-2		TN017E0-2		TN017E0-2		TN017E0-2		TN017E0-2		A0300NF		A0300NF		A0300NF		A0300NF		A0300NF					
	Package			U-DFN3030-8(Type E)		U-DFN3030-8(Type E)		U-DFN3030-8(Type E)		U-DFN3030-8(Type E)		U-DFN3030-8(Type E)		U-DFN3030-8(Type E)		U-DFN3030-8(Type E)		U-DFN3030-8(Type E)		U-DFN3030-8(Type E)		U-DFN3030-8(Type E)		X2-DFN1010-4		X2-DFN1010-4		X2-DFN1010-4		X2-DFN1010-4		X2-DFN1010-4					
	Wire Bond, Cu Piller, CSP			Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond			
	MSL Level			1		1		1		1		1		1		1		1		1		1		1		1		1		1		1		1			
	Die Quantity (eg. Die per package)			1		1		1		1		1		1		1		1		1		1		1		1		1		1		1		1			
	Die Name(1)			AD08070637C0-SP-ADJ-LC		AD08070637C0-SP-ADJ-LC		AD08070637C0-SP-ADJ-LC		TN017E0-2-01A-LC		TN017E0-2-01A-LC		TN017E0-2-01A-LC		AD06070457A0		TN017E0-2-33A-LC		TN017E0-2-33A-LC		TN017E0-2-33A-LC		AD08070300NF-SP SPFAB wafer Name		AD08070300NF-SP SPFAB wafer Name		AD08070300NF-SP SPFAB wafer Name		AD08070300NF-SP SPFAB wafer Name		AD08070300NF-SP SPFAB wafer Name		AD08070300NF-SP SPFAB wafer Name			
	Die Size (W/L/Thickness)			0.73*0.64*0.6mm		0.73*0.64*0.6mm		0.73*0.64*0.6mm		0.745*0.785*0.675mm		0.745*0.785*0.675mm		0.745*0.785*0.675mm		0.745*0.785*0.675mm		0.745*0.785*0.675mm		0.745*0.785*0.250mm m		0.745*0.785*0.250mm		0.745*0.785*0.250mm		490um*490um*100um		490um*490um*100um		490um*490um*100um		490um*490um*100um		490um*490um*100um			
	Die Process / Technology			SP18BC		SP18BC		SP18BC		0.5um/5V/1P3M CMOS		0.5um/5V/1P3M CMOS		0.5um/5V/1P3M CMOS		0.5um/5V/1P3M CMOS		0.5um/5V/1P3M CMOS		0.5um/5V/1P3M CMOS		0.5um/5V/1P3M CMOS		0.18um CMOS SP180AN, SP18BCSV_3LM		0.18um CMOS SP180AN, SP18BCSV_3LM		0.18um CMOS SP180AN, SP18BCSV_3LM		0.18um CMOS SP180AN, SP18BCSV_3LM		0.18um CMOS SP180AN, SP18BCSV_3LM		0.18um CMOS SP180AN, SP18BCSV_3LM			
Fab	No of masks Steps			21		21		21		PdCu		PdCu		PdCu		PdCu		PdCu		PdCu		PdCu		PdCu		20		20		20		20		20			
	Wire Bond Material (Au, Cu, Al)			PdCu		PdCu		PdCu		1.0mil		1.0mil		1.0mil		1.0mil		1.0mil		1.0mil		1.0mil		1.0mil		0.8mil		0.8mil		0.8mil		0.8mil		0.8mil			
	Wire Diameter			1.0mil		1.0mil		1.0mil		SPFAB		SPFAB		SPFAB		SPFAB		BCD SFABII		SPFAB		SPFAB		SPFAB		SPFAB		SPFAB		SPFAB		SPFAB		SPFAB			
	Wafer FAB Location			USA		USA		USA		USA		China		China		China		China		China		China		China		USA		USA		USA		USA		USA			
	Wafer Diameter			200		200		200		6"		6"		6"		6"		6"		6"		6"		6"		6"		6"		6"		6"		6"		6"	
	Wafer Thickness			675um		675um		675um		675um		675um		675um		675um		675um		675um		675um		675um		725um		725um		725um		725um		725um		725um	
	Top Metal Type/Bond Pad Composition			Al/Cu		Al/Cu		Al/Cu		Al/Cu		Al/Cu		Al/Cu		Al/Cu		Al/Cu		Al/Cu		Al/Cu		Aluminum 0.5% Cu		Aluminum 0.5% Cu		Aluminum 0.5% Cu		Aluminum 0.5% Cu		Aluminum 0.5% Cu		Aluminum 0.5% Cu		Aluminum 0.5% Cu	
	Top Metal Thickness			2.7 um		2.7 um		2.7 um		3 um		3 um		3 um		3 um		3 um		3 um AlCu		3 um AlCu		3 um AlCu		2.7um		2.7um		2.7um		2.7um		2.7um		2.7um	
	Die Passivation thickness range			SIN 0.5um+SiO2 0.5um		SIN 0.5um+SiO2 0.5um		SIN 0.5um+SiO2 0.5um		SIN 0.5um+SiO2 0.5um		SIN 0.5um+SiO2 0.5um		SIN 0.5um+SiO2 0.5um		SIN 0.5um+SiO2 0.5um		SIN 0.5um+SiO2 0.5um		SIN 0.5um+SiO2 0.5um		SIN 0.5um+SiO2 0.5um		SIN 5000A +/- 500A; 8000 SiO2 +/- 800A.		SIN 5000A +/- 500A; 8000 SiO2 +/- 800A.		SIN 5000A +/- 500A; 8000 SiO2 +/- 800A.		SIN 5000A +/- 500A; 8000 SiO2 +/- 800A.		SIN 5000A +/- 500A; 8000 SiO2 +/- 800A.		SIN 5000A +/- 500A; 8000 SiO2 +/- 800A.			
	No. of bond over active area			0		0		0		0		0		0		0		0		0		0		4		4		4		4		4		4			
	Glass Transition Temp			130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C		130 degree C			
	Max Junction Temp			150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C		150 degree C			
	No of masks Steps			22		22		22		17		17		17		17		17		17		17		20		20		20		20		20		20			
	Metal Layers			3		3		3		3		3		3		3		3		3		3		3		3		3		3		3		3			
	Saw Operation Site			CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		NA		NA		NA		NA		NA		NA			
	Backgrind Thickness			140um		140um		140um		140um		140um		140um		140um		250um		250um		250um		CAT		CAT		CAT		CAT		CAT		CAT			
	Backgrind Location			CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT		CAT			
	Bond Type (at Die)			Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball			
	Bond Type (at LP)			Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge			
	DB Epoxy/Solder Type			Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy		Epoxy			
	Die Attach Material			QMI519		QMI519		QMI519		QMI519		QMI519		QMI519		QMI519		QMI519		900SSP(导电胶)		900SSP(导电胶)		900SSP(导电胶)		QMI5											